FFPF10F150S

10 A, 1500 V, Damper Diode

Features

- High Speed Recovery t_{RR} = 170 ns (@ I_F = 1 A)
- Max Forward Voltage, V_F = 1.6 V (@ T_C = 25°C)
- 1500 V Reverse Voltage and High Reliability
- Low Forward Voltage
- This Device is Pb−Free and is RoHS Compliant

Applications

- Suitable for Damper Diode in Horizontal Deflection Circuits

ABSOLUTE MAXIMUM RATINGS

T_C = 25°C unless otherwise noted

Symbol	Parameter	Rating	Unit
V_{RRM}	Peak Repetitive Reverse Voltage	1500	V
V_{RWM}	Working Peak Reverse Voltage	1500	V
$I_{F(AV)}$	Average Rectified Forward Current @ T_C = 125°C	10	A
I_{FSM}	Non−repetitive Peak Surge Current 60Hz Single Half−Sine Wave	100	A
T_J, T_{STG}	Operating Junction and Storage Temperature	− 65 to +175	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

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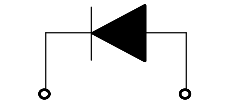
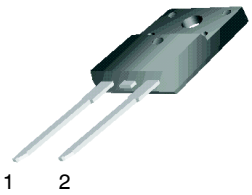
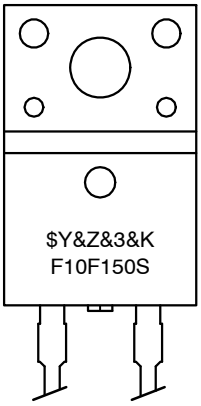


1. Cathode 2. Anode



TO−220, 2−Lead
CASE 221AS

MARKING DIAGRAM



$Y	= ON Semiconductor Logo
&Z&3	= Data Code (Year & Week)
&K	= Lot
F10F150S	= Specific Device Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

THERMAL CHARACTERISTICS T_C = 25°C unless otherwise noted

Symbol	Parameter	Max.	Unit
$R_{\theta JC}$	Maximum Thermal Resistance, Junction to Case	3.0	°C/W

PACKAGE MARKING AND ORDERING INFORMATION

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FFPF10F150STU	F10F150S	TO−220F−2L	Tube	N/A	N/A	30

ELECTRICAL CHARACTERISTICS T_C = 25°C unless otherwise noted

Parameter	Conditions		Min.	Typ.	Max.	Unit
V_F (Note 1)	Maximum Instantaneous Forward Voltage I_F = 10 A I_F = 10 A	 T_C = 25°C T_C = 125°C	 – –	 – –	 1.6 1.4	V
I_R (Note 1)	Maximum Instantaneous Reverse Current @ rated V_R	 T_C = 25°C T_C = 125°C	 – –	 – –	 10 80	μA
t_{RR}	Maximum Reverse Recovery Time (I_F = 1 A, di_F/dt = 50 A/μs, V_R = 30 V)		–	–	170	ns
t_{FR}	Maximum Forward Recovery Time (I_F = 6.5 A, di_F/dt = 50 A/μs)		–	–	250	ns
V_{FRM}	Maximum Forward Recovery Voltage		–	–	14	V

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Pulse: Test Pulse Width = 300 μs, Duty Cycle = 2%

Test Circuit and Waveforms

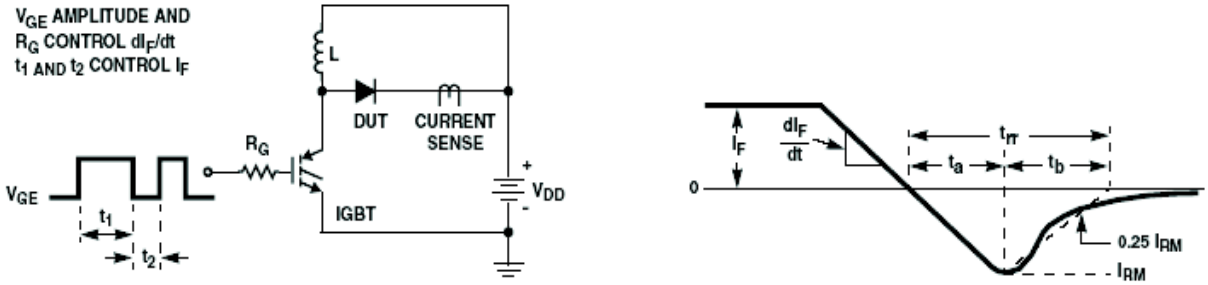


Figure 1. Diode Reverse Recovery Test Circuit & Waveform

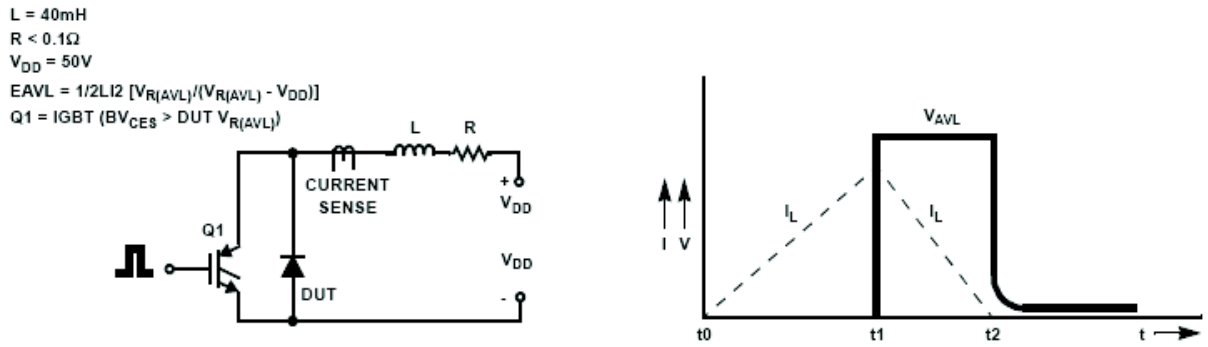


Figure 2. Unclamped Inductive Switching Test Circuit & Waveform

TYPICAL CHARACTERISTICS

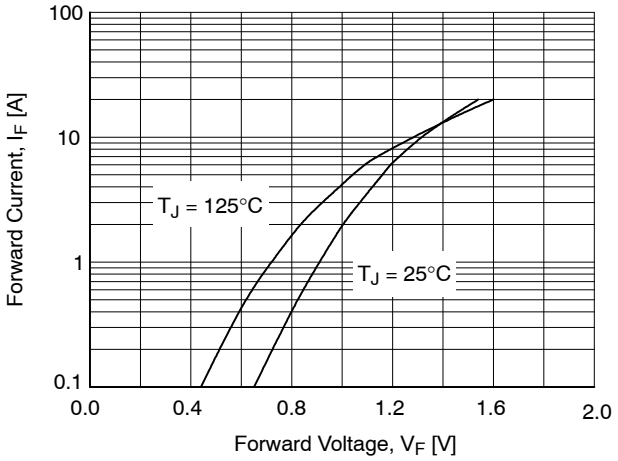


Figure 3. Typical Forward Voltage Drop

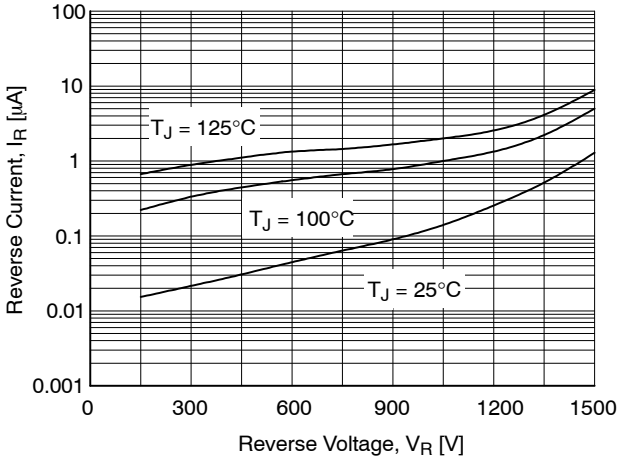


Figure 4. Typical Reverse Current

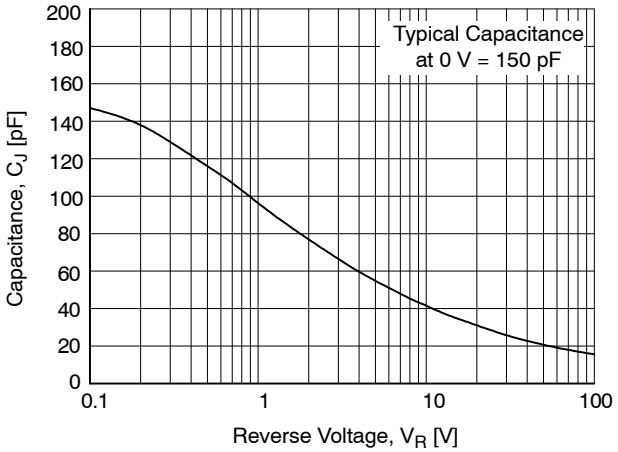


Figure 5. Typical Junction Capacitance

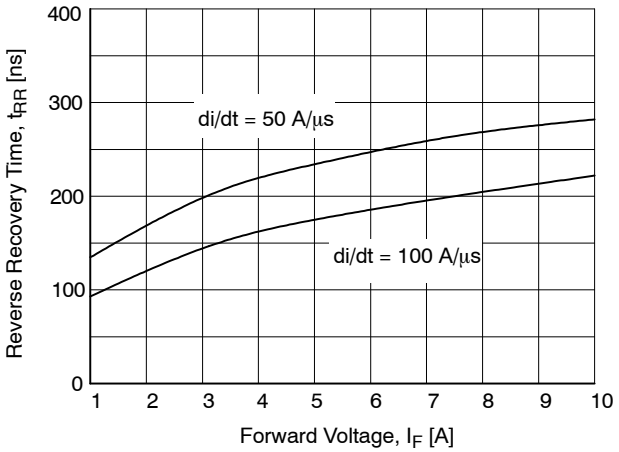


Figure 6. Typical Reverse Recovery Time

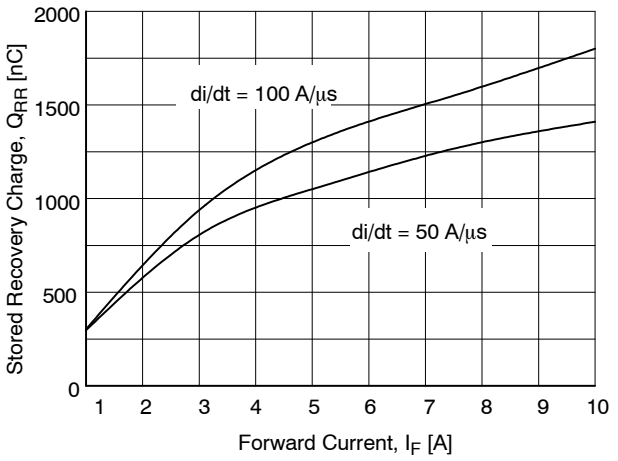


Figure 7. Typical Stored Charge

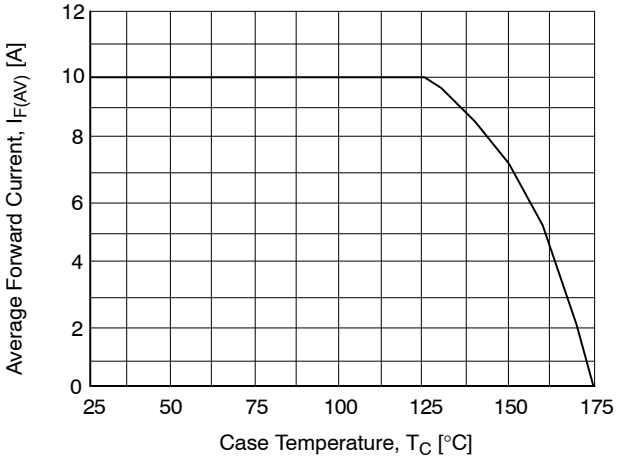


Figure 8. Forward Current Deration Curve

MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS

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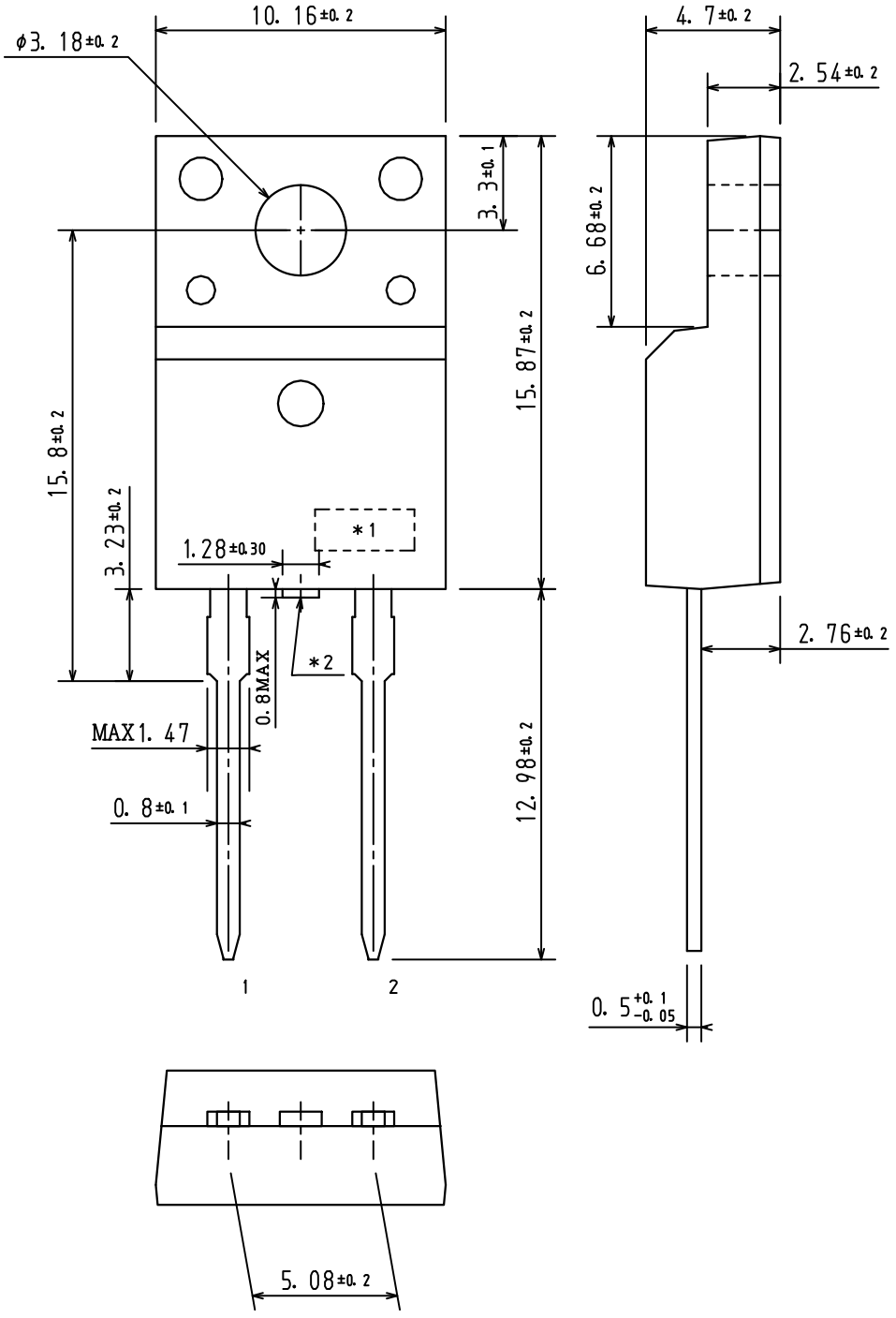

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DESCRIPTION:	**TO−220 FULLPACK, 2−LEAD / TO−220F−2FS**	**PAGE 1 OF 1**

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